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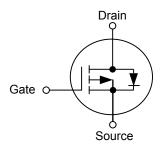
Power MOSFET

P-CHANNEL ENHANCEMENT MODE

DESCRIPTION

The UTC **UT9435H** provide excellent $R_{DS(ON)}$, low gate charge and fast switching speed. It has been optimized for power management applications.

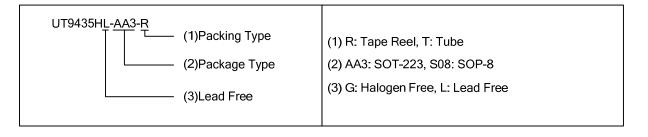
SYMBOL



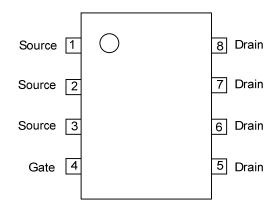
SOP-8

ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment						Decking		
Lead Free	Halogen Free	Package	1	2	З	4	5	6	7	8	Packing
UT9435HL-AA3-R	UT9435HG-AA3-R	SOT-223	G	D	S	I	I	I	1	I	Tape Reel
UT9435HL-S08-R	UT9435HG-S08-R	SOP-8	ഗ	ഗ	ഗ	G	D	D	D	D	Tape Reel
UT9435HL-S08-T	UT9435HG-S08-T	SOP-8	S	S	S	G	D	D	D	D	Tube



■ PIN CONFIGURATION





■ ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNITS
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 3)	T _A =125℃	I _D	±5.3	Α
Pulsed Drain Current (Note 1, 2)		I _{DM}	±20	Α
Power Dissipation		PD	2.5	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	50	°C /W

■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

	i	1	+						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0 V, I _D =-250 μA	-30			V			
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-24 V, V _{GS} =0 V			-1	μA			
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0 V, V _{GS} = ±20V			±100	nA			
ON CHARACTERISTICS									
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250 μA	-1		-3	V			
	R _{DS(ON)}	V _{GS} =-10V, I _D =-5.3A		44	50	mΩ			
Drain-Source On-State Resistance (Note 2)		V _{GS} =-4.5V, I _D =-4.2A		74	90	mΩ			
On State Drain Current	I _{D(ON)}	V _{DS} = -5V, V _{GS} =-10V	-20			А			
DYNAMIC PARAMETERS									
Input Capacitance	CISS			1040		pF			
Output Capacitance	Coss	V _{DS} =-15V, V _{GS} =0V,		420		pF			
Reverse Transfer Capacitance	C _{RSS}	f=1.0MHz		150		pF			
SWITCHING PARAMETERS									
Turn-ON Delay Time (Note 2)	t _{D(ON)}			19	26	ns			
Turn-ON Rise Time	t _R	V _{DD} =-15V, I _D =-1A,		9	13	ns			
Turn-OFF Delay Time	t _{D(OFF)}	V _{GEN} =-10V, R _G =6Ω		74	105	ns			
Turn-OFF Fall Time	t⊨			36	50	ns			
Total Gate Charge (Note 2)	Q_{G}			22.5	29	nC			
Gate-Source Charge	Q _{GS}	$V_{DS} = -15V, V_{GS} = -10V,$		2		nC			
Gate-Drain Charge	Q_{GD}	I _D =-4.6A		6		nC			
DRAIN-SOURCE DIODE CHARACTERISTICS									
Drain-Source Diode Forward Voltage(Note 2)	V _{SD}	V _{GS} =0V, I _S =-5.3A		-0.84	-1.3	V			

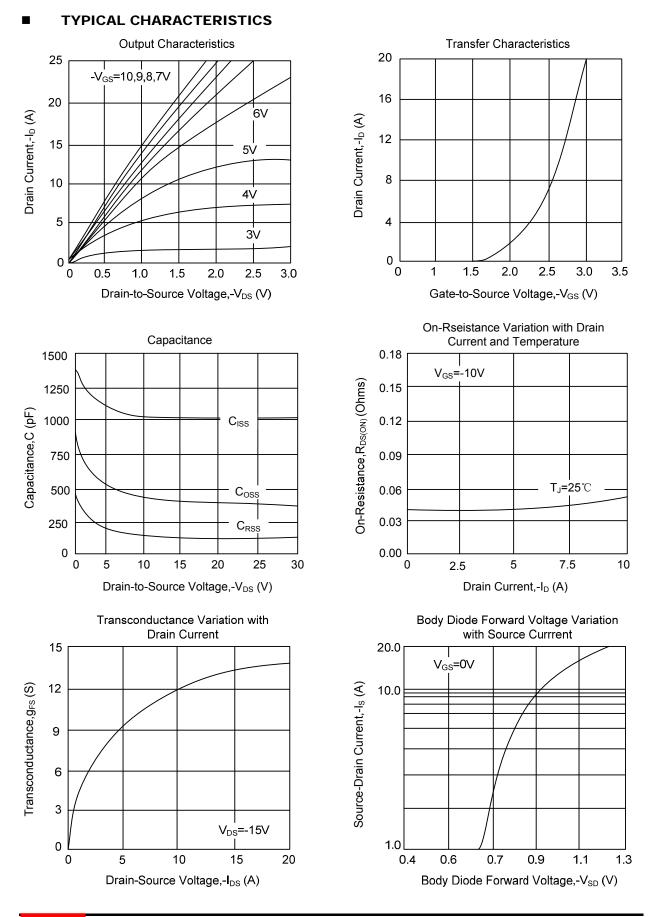
Notes: 1. Pulse width limited by $T_{J(MAX)}$

2. Pulse width \leq 300us, duty cycle \leq 2%.

3. Surface mounted on 1 in² copper pad of FR4 board

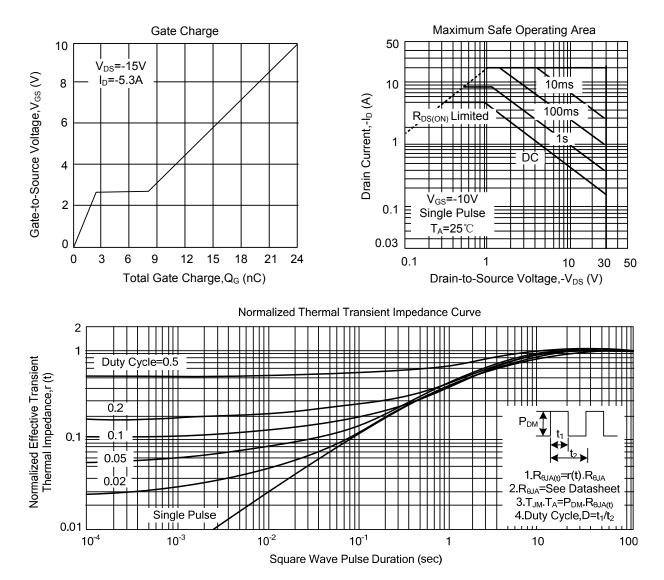


Power MOSFET





TYPICAL CHARACTERISTICS(Cont.)



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